

Vishay Semiconductors

RoHS

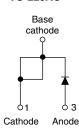
COMPLIANT

HALOGEN

FREE

HEXFRED[®] Ultrafast Soft Recovery Diode, 25 A





PRODUCT SUMMARY						
Package	TO-220AC					
I _{F(AV)}	25 A					
V _R	600 V					
V _F at I _F	1.7 V					
t _{rr} typ.	23 ns					
T _J max.	150 °C					
Diode variation	Single die					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA25TB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25TB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25TB60... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Cathode to anode voltage	V _R		600	V						
Maximum continuous forward current	I _F	T _C = 100 °C	25							
Single pulse forward current	I _{FSM}		225	А						
Maximum repetitive forward current	I _{FRM}		100							
Movimum power dissinction	р	T _C = 25 °C	125	w						
Maximum power dissipation	P _D	T _C = 100 °C	50	vv						
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C						

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-			
Maximum forward voltage		I _F = 25 A		-	1.3	1.7	V		
	V _{FM}	I _F = 50 A	See fig. 1	-	1.5	2.0			
		I _F = 25 A, T _J = 125 °C		-	1.3	1.7			
Maximum reverse		$V_{R} = V_{R}$ rated	See fig. 0	-	1.5	20			
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	600	2000	μΑ		
Junction capacitance	CT	V _R = 200 V See fig. 3		-	55	100	pF		
Series inductance	L _S	Measured lead to lead 5 mm from body	-	8.0	-	nH			

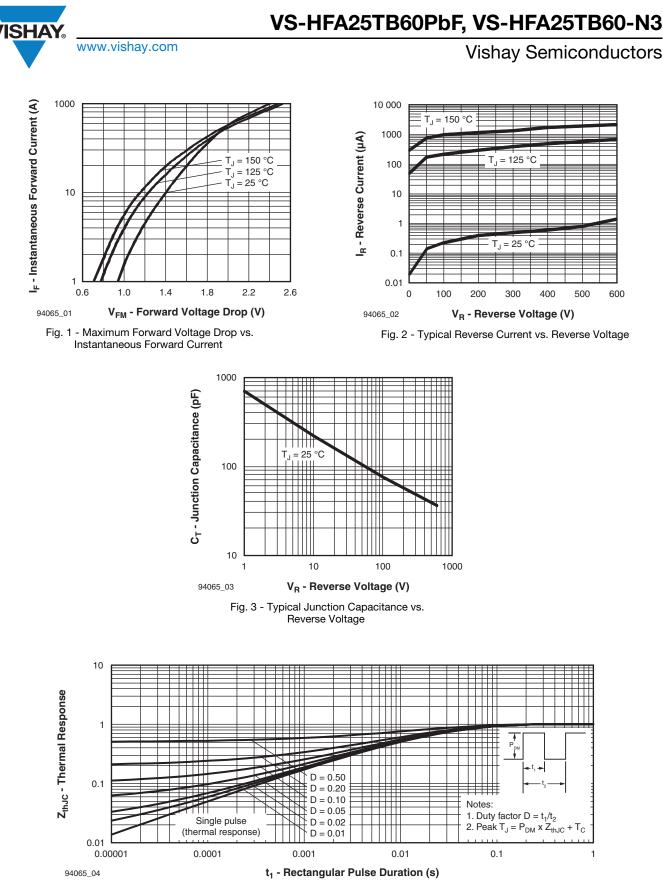
DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time See fig. 5, 6 and 16	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	0 A/μs, V _R = 30 V	-	23	-	ns		
	t _{rr1}	T _J = 25 °C	I _F = 25 A dI _F /dt = 200 A/μs V _R = 200 V	-	50	75			
	t _{rr2}	T _J = 125 °C		-	105	160			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	10	A nC		
See fig. 7 and 8	I _{RRM2}	T _J = 125 °C		-	8.0	15			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	112	375			
See fig. 9 and 10	Q _{rr2}	T _J = 125 °C		-	420	1200	ne		
Peak rate of fall of recovery current during t_b See fig. 11 and 12	dl _{(rec)M} /dt1	T _J = 25 °C		-	250	-	A∕µs		
	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	γγµs		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	1.0					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount		-	80	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-					
Weight			-	2.0	-	g				
vveignt			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-220AC		HFA2	5TB60					

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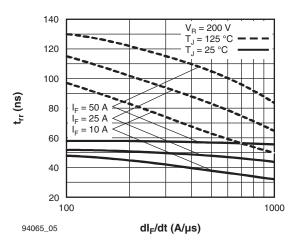


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Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

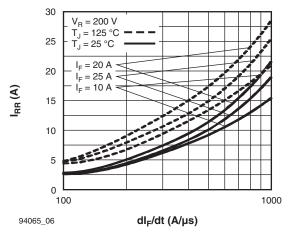


Fig. 6 - Typical Recovery Current vs. dl_F/dt

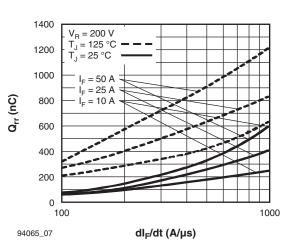
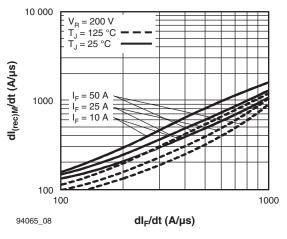


Fig. 7 - Typical Stored Charge vs. dl_F/dt





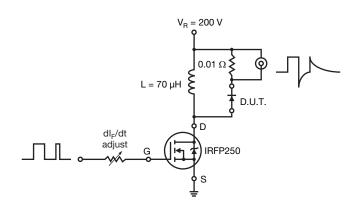


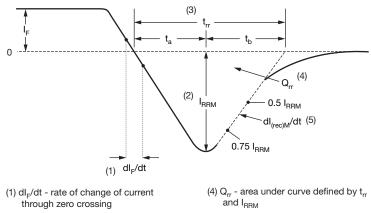
Fig. 9 - Reverse Recovery Parameter Test Circuit

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(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 $\mathrm{I}_{\mathrm{RRM}}$ and 0.50 $\mathrm{I}_{\mathrm{RRM}}$ extrapolated to zero current.

HF

2

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

PbF

7

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

60

6

ΤВ

5

Fig. 10 - Reverse Recovery Waveform and Definitions

25

4

ORDERING INFORMATION TABLE

Device code VS-1

2

3

4

5

6 7

1	- Visha	y Semiconductors	product
1	- visna	y Semiconductors	produc

Α

3

- HEXFRED[®] family
- Electron irradiated

Current rating (25 = 25 A)

Package:

TB = TO-220AC

Voltage rating (60 = 600 V)

Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESC									
VS-HFA25TB60PbF	50	1000	Antistatic plastic tube						
VS-HFA25TB60-N3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS							
Dimensions		www.vishay.com/doc?95221					
Part marking information	TO-220ACPbF	www.vishay.com/doc?95224					
	TO-220AC-N3	www.vishay.com/doc?95068					
SPICE model		www.vishay.com/doc?95468					

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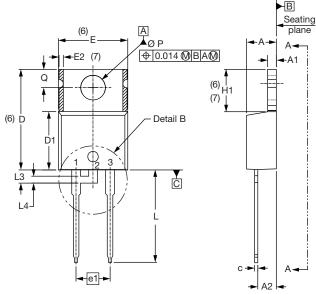


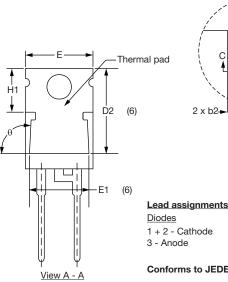
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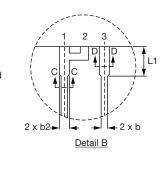
TO-220AC

plane

DIMENSIONS in millimeters and inches









Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

⊕ 0.015 **()** BA()

SYMBOL	MILLIM	IETERS	INC	HES	NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040			e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4		H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068			L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4		L1	3.32	3.82	0.131	0.150	2
С	0.36	0.61	0.014	0.024			L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4		L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3		ØΡ	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6		θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6							

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1
- ⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

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For technical questions within your region, please contact one of the following: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com



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